IXYS

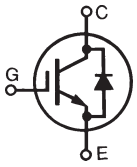
Preliminary Technical Information

XPT™ 600V IGBT GenX3™ w/Diode

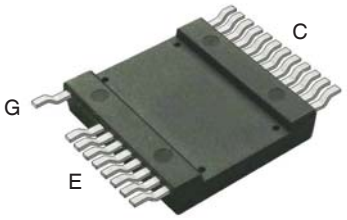
MMIX1X200N60B3H1

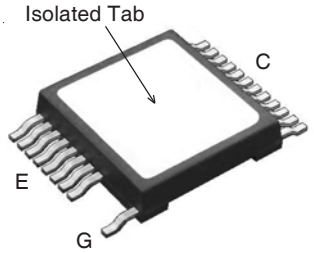
V_{CES} = 600V
I_{C110} = 72A
$V_{CE(sat)}$ ≤ 1.7V
$t_{fi(typ)}$ = 110ns

(Electrically Isolated Tab)



Extreme Light Punch Through
IGBT for 10-30kHz Switching





G = Gate E = Emitter
C = Collector

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	T_J = 25°C to 150°C	600	V
V_{CGR}	T_J = 25°C to 150°C, R_{GE} = 1MΩ	600	V
V_{GES}	Continuous	±20	V
V_{GEM}	Transient	±30	V
I_{C25}	T_C = 25°C (Chip Capability)	175	A
I_{C110}	T_C = 110°C	72	A
I_{F110}	T_C = 110°C	28	A
I_{CM}	T_C = 25°C, 1ms	1000	A
I_A	T_C = 25°C	100	A
E_{AS}	T_C = 25°C	1	J
SSOA (RBSOA)	V_{GE} = 15V, T_{VJ} = 150°C, R_G = 1Ω Clamped Inductive Load	I_{CM} = 400 @$V_{CE} \leq V_{CES}$	A
t_{sc} (SCSOA)	V_{GE} = 15V, V_{CE} = 360V, T_J = 150°C R_G = 10Ω, Non Repetitive	10	μs
P_C	T_C = 25°C	520	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	Maximum Lead Temperature for Soldering	300	°C
T_{SOLD}	1.6 mm (0.062 in.) from Case for 10	260	°C
V_{ISOL}	50/60Hz, 1 minute	2500	V~
F_C	Mounting Force	50..200/11..45	N/lb.
Weight		8	g

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{CES}	I_C = 250μA, V_{GE} = 0V	600			V
$V_{GE(th)}$	I_C = 250μA, V_{CE} = V_{GE}	3.5		6.0	V
I_{CES}	V_{CE} = V_{CES}, V_{GE} = 0V			50	μA
	Note 2, T_J = 150°C			3	mA
I_{GES}	V_{CE} = 0V, V_{GE} = ±20V			±200	nA
$V_{CE(sat)}$	I_C = 100A, V_{GE} = 15V, Note 1		1.40	1.70	V
	T_J = 150°C		1.58		V

Features

- Silicon Chip on Direct-Copper Bond (DCB) Substrate
- Isolated Mounting Surface
- 2500V~ Electrical Isolation
- Optimized for Low Conduction and Switching Losses
- Avalanche Rated
- Short Circuit Capability
- Very High Current Capability
- Square RBSOA

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	I_C = 60A, V_{CE} = 10V, Note 1	27	45		S
C_{ies}	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz		9970		pF
C_{oes}			570		pF
C_{res}			183		pF
$Q_{g(on)}$	I_C = 200A, V_{GE} = 15V, V_{CE} = 0.5 • V_{CES}		315		nC
Q_{ge}			98		nC
Q_{gc}			130		nC
$t_{d(on)}$	**Inductive load, T_J = 25°C**		48		ns
t_{ri}	I_C = 100A, V_{GE} = 15V		100		ns
E_{on}	V_{CE} = 360V, R_G = 1Ω		2.85		mJ
$t_{d(off)}$	Note 3		160		ns
t_{fi}			110		ns
E_{off}			2.90	4.40	mJ
$t_{d(on)}$	**Inductive load, T_J = 150°C**		46		ns
t_{ri}	I_C = 100A, V_{GE} = 15V		94		ns
E_{on}	V_{CE} = 360V, R_G = 1Ω		4.40		mJ
$t_{d(off)}$	Note 3		180		ns
t_{fi}			215		ns
E_{off}			3.45		mJ
R_{thJC}				0.24	°C/W
R_{thCS}			0.05		°C/W

Reverse Diode (FRED)

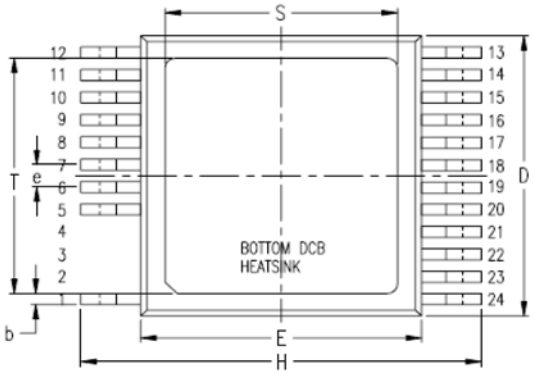
Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
V_F	I_F = 100A, V_{GE} = 0V, Note 1			2.5	V
	T_J = 150°C		2.3		V
I_{RM}	I_F = 100A, V_{GE} = 0V, T_J = 150°C		95		A
t_{rr}	$-di_F/dt$ = 1500A/μs, V_R = 300V		100		ns
R_{thJC}				0.83	°C/W

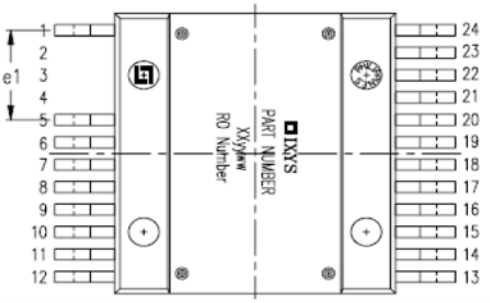
Notes:

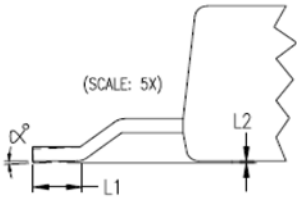
1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.
2. Part must be heatsunk for high-temp I_{CES} measurement.
3. Switching times & energy losses may increase for higher V_{CE}(Clamp), T_J or R_G.

PRELIMANARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.







SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.209	.224	5.30	5.70
A1	.154	.161	3.90	4.10
A2	.055	.063	1.40	1.60
b	.035	.045	0.90	1.15
c	.018	.026	0.45	0.65
D	.976	.994	24.80	25.25
E	.898	.915	22.80	23.25
E1	.543	.559	13.80	14.20
e	.079 BSC		2.00 BSC	
e1	.315 BSC		8.00 BSC	
H	1.272	1.311	32.30	33.30
L	.181	.209	4.60	5.30
L1	.051	.067	1.30	1.70
L2	.000	.006	0.00	0.15
S	.736	.760	18.70	19.30
T	.815	.839	20.70	21.30
α	0	4°	0	4°

PIN: 1 = Gate
5-12 = Emitter
13-24 = Collector

Fig. 1. Output Characteristics @ T_J = 25ºC

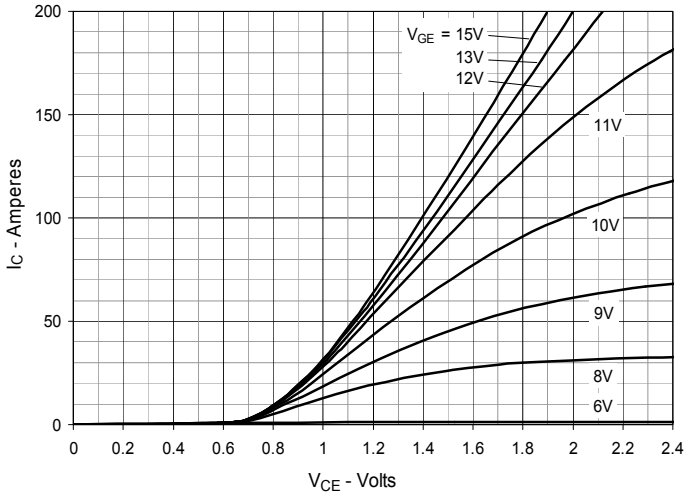


Fig. 2. Extended Output Characteristics @ T_J = 25ºC

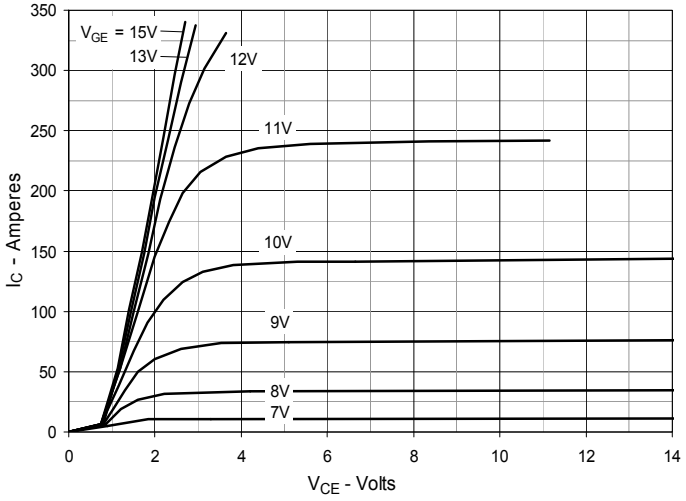


Fig. 3. Output Characteristics @ T_J = 150ºC

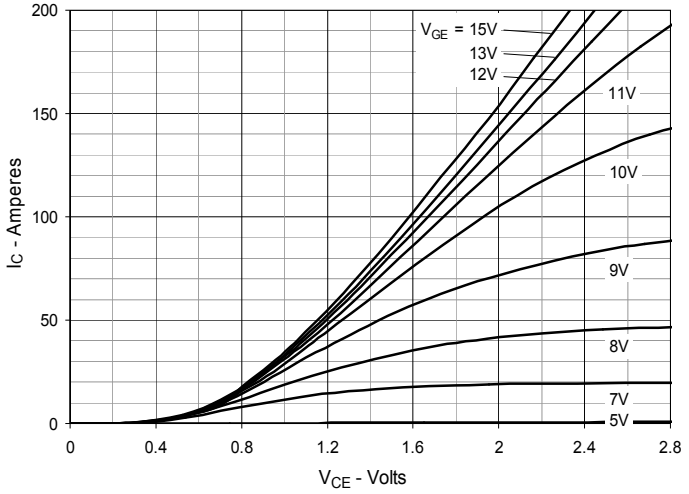


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

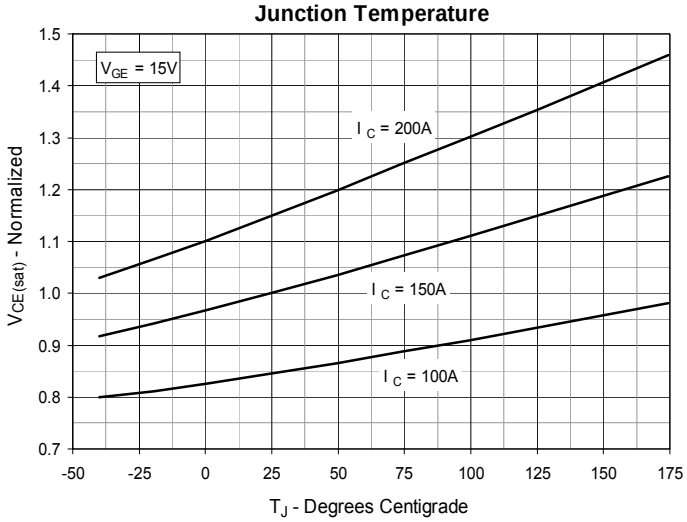


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

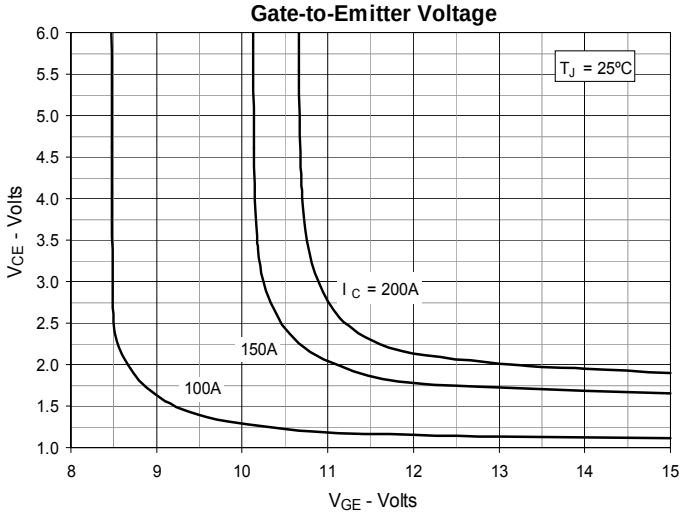


Fig. 6. Input Admittance

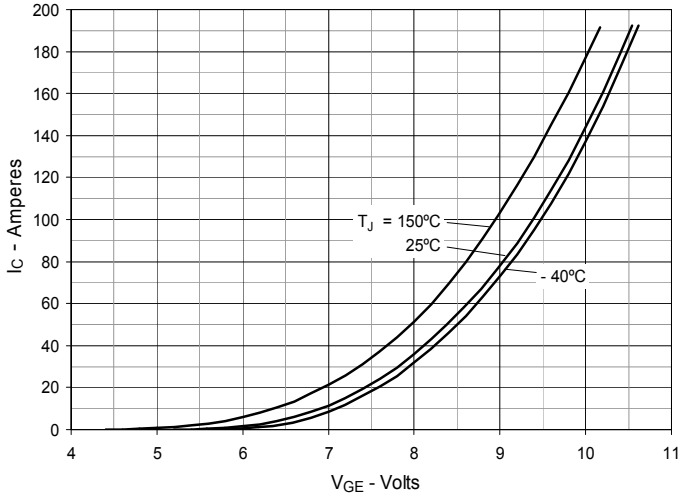


Fig. 7. Transconductance

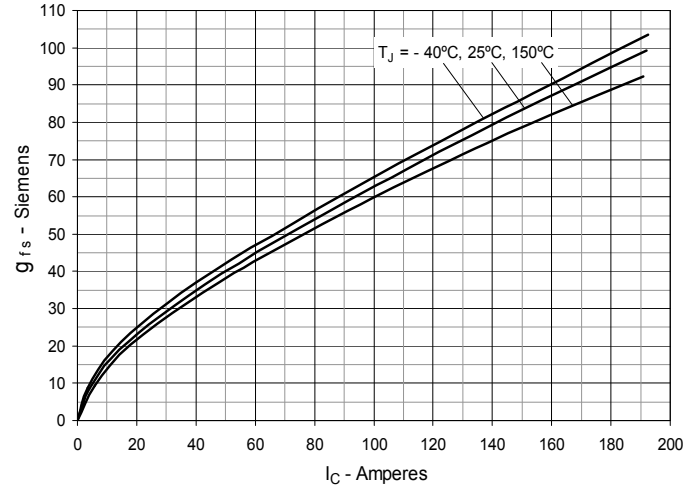


Fig. 8. Gate Charge

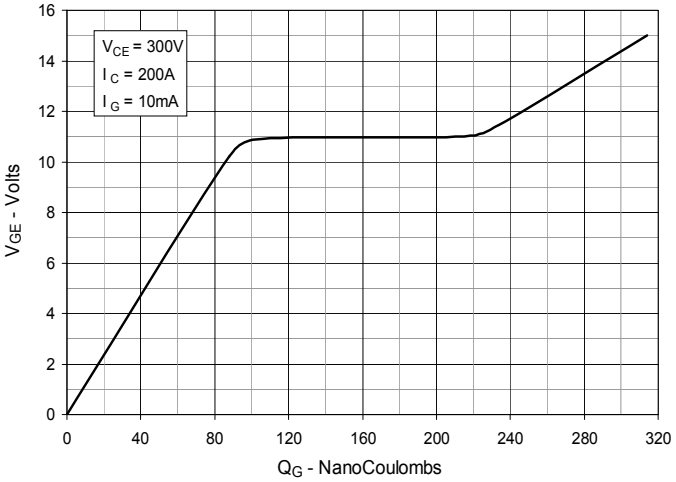


Fig. 9. Capacitance

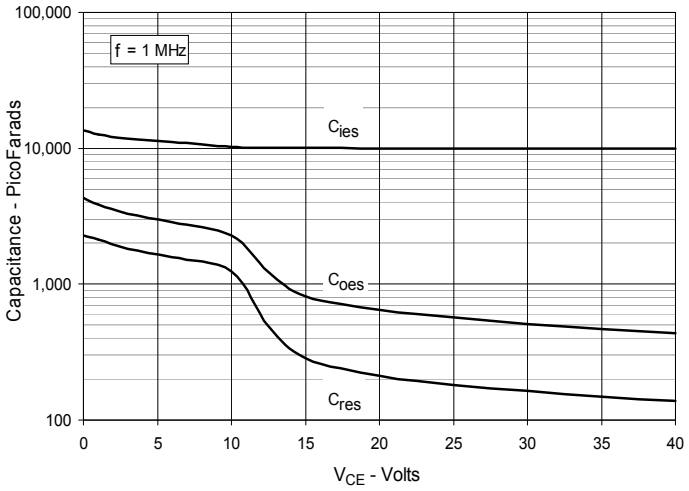


Fig. 10. Reverse-Bias Safe Operating Area

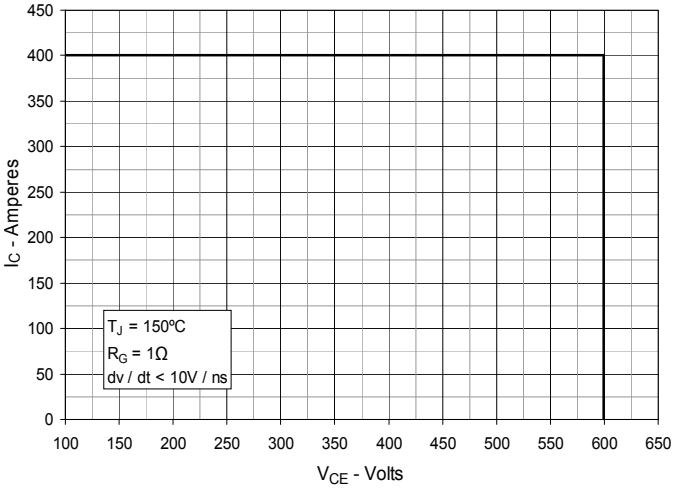


Fig. 11. Forward-Bias Safe Operating Area

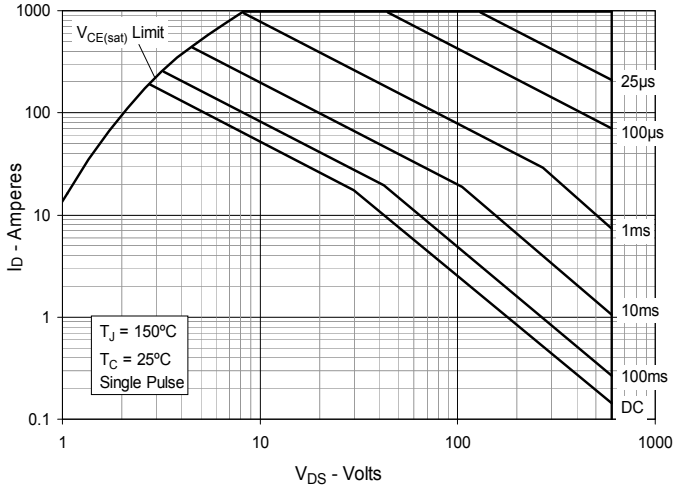


Fig. 12. Maximum Transient Thermal Impedance

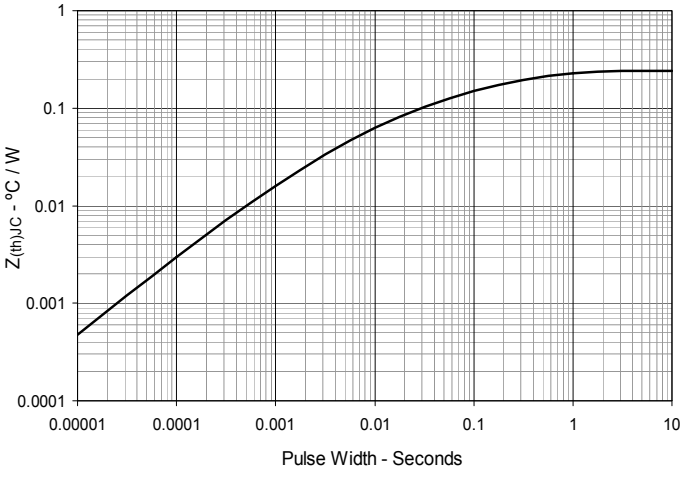


Fig. 13. Inductive Switching Energy Loss vs. Gate Resistance

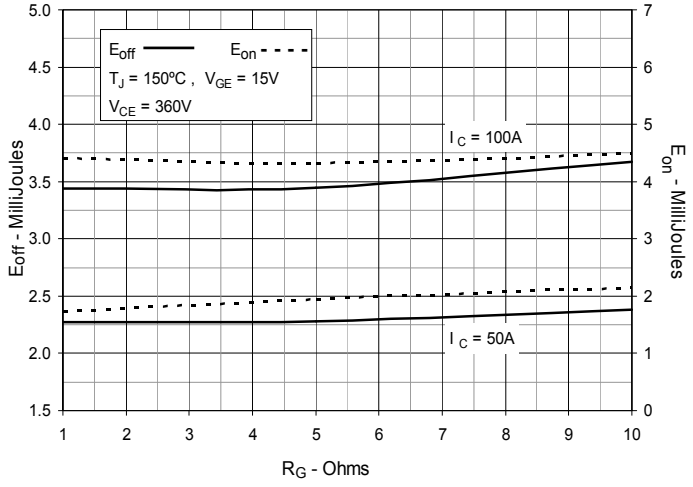


Fig. 14. Inductive Switching Energy Loss vs. Collector Current

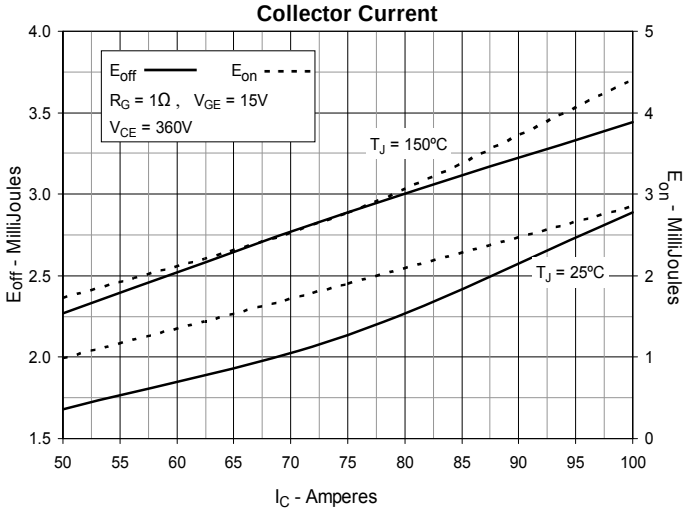


Fig. 15. Inductive Switching Energy Loss vs. Junction Temperature

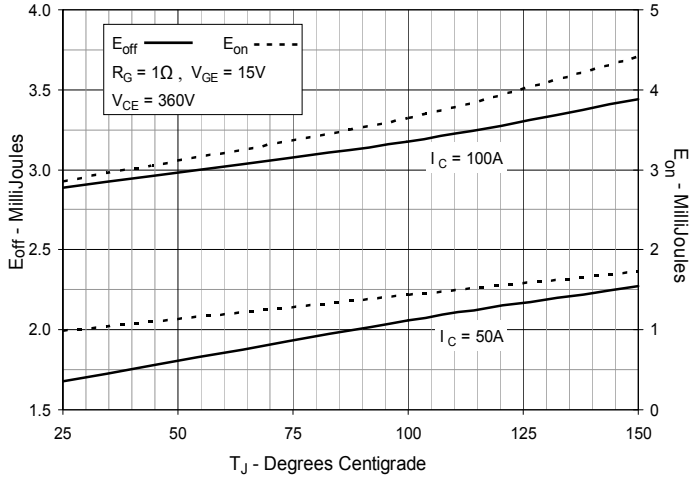


Fig. 16. Inductive Turn-off Switching Times vs. Gate Resistance

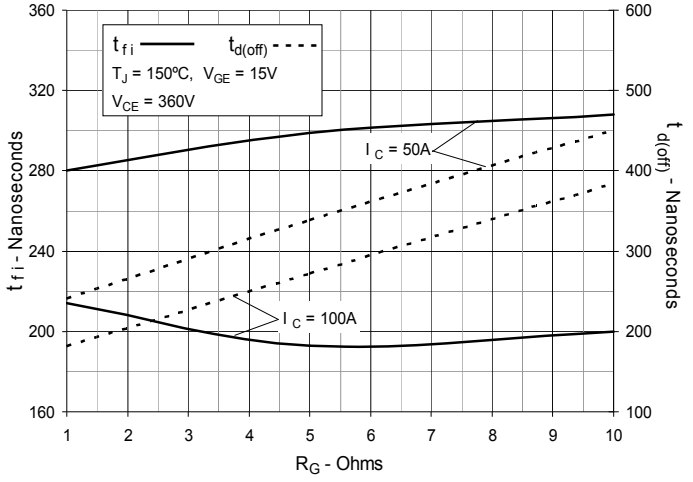


Fig. 17. Inductive Turn-off Switching Times vs. Collector Current

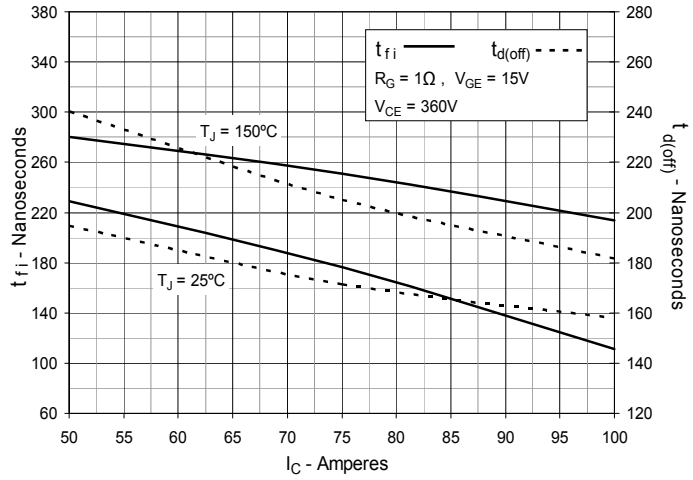


Fig. 18. Inductive Turn-off Switching Times vs. Junction Temperature

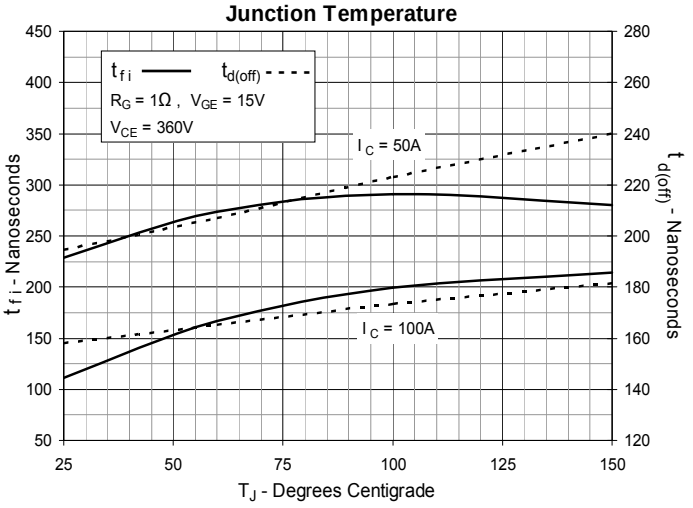


Fig. 19. Inductive Turn-on Switching Times vs. Gate Resistance

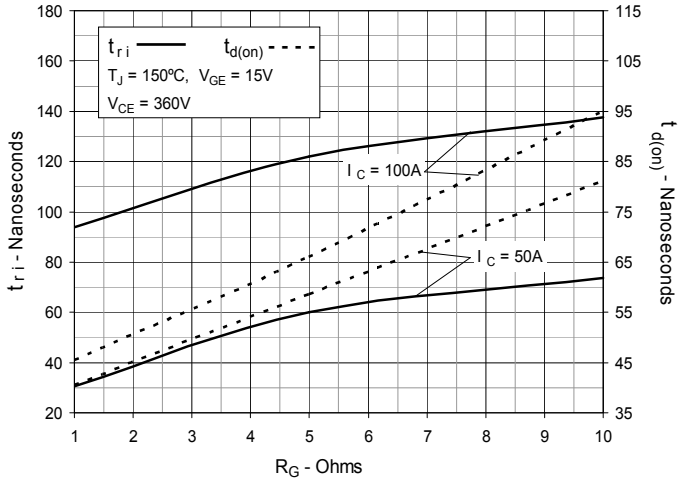


Fig. 20. Inductive Turn-on Switching Times vs. Collector Current

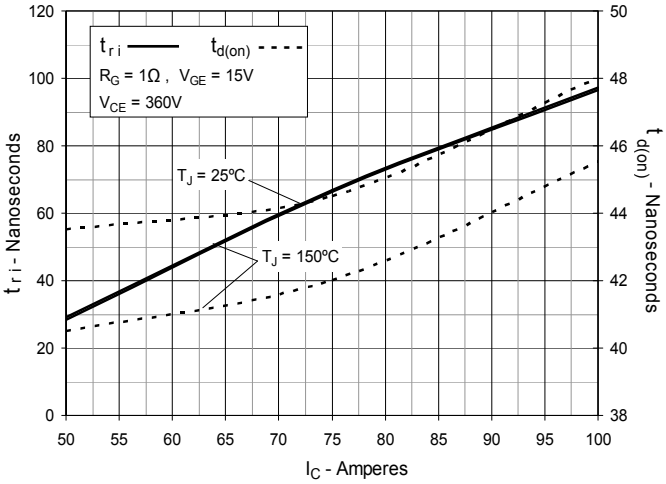


Fig. 21. Inductive Turn-on Switching Times vs. Junction Temperature

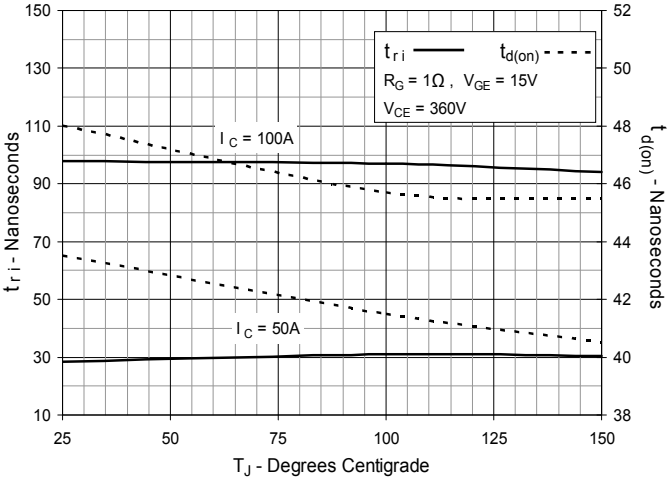


Fig. 22. Typ. Forward characteristics

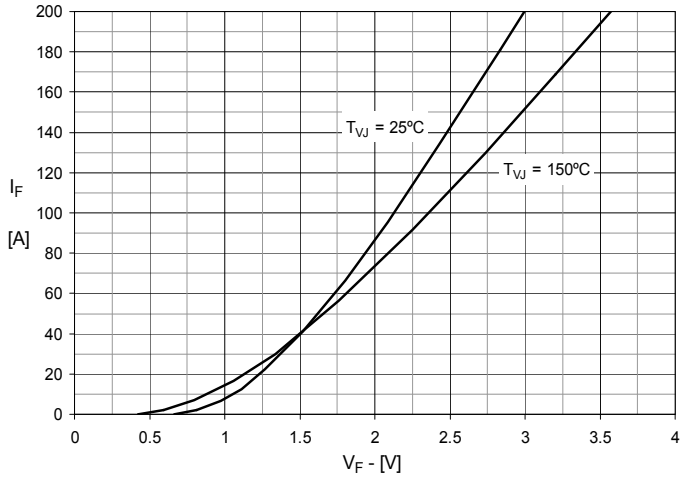


Fig. 23. Typ. Reverse Recovery Charge Q_{rr} vs. $-di_F/dt$

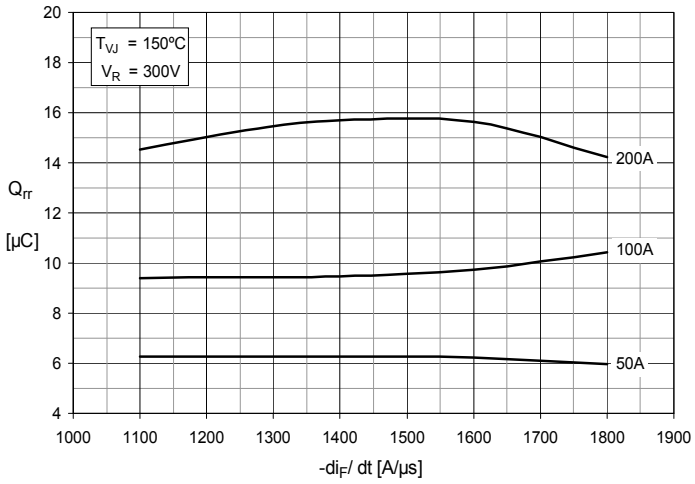


Fig. 24. Typ. Peak Reverse Current I_{RM} vs. $-di_F/dt$

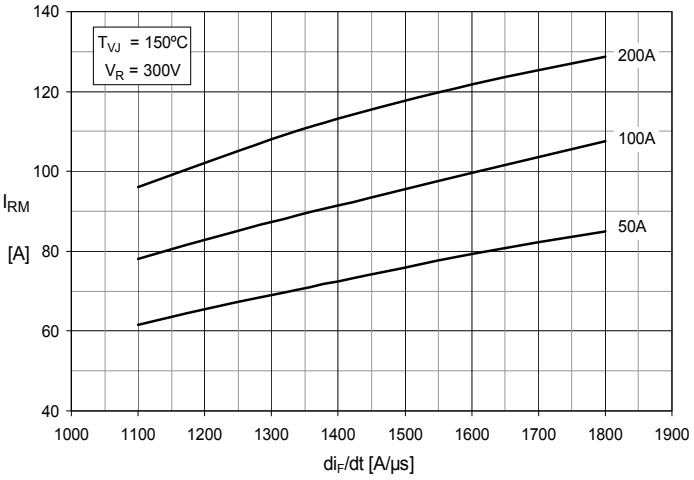


Fig. 25. Typ. Recovery Time t_{rr} vs. $-di_F/dt$

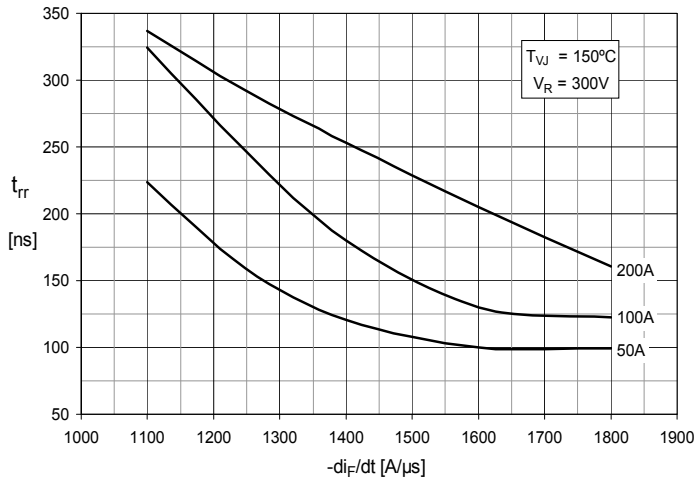
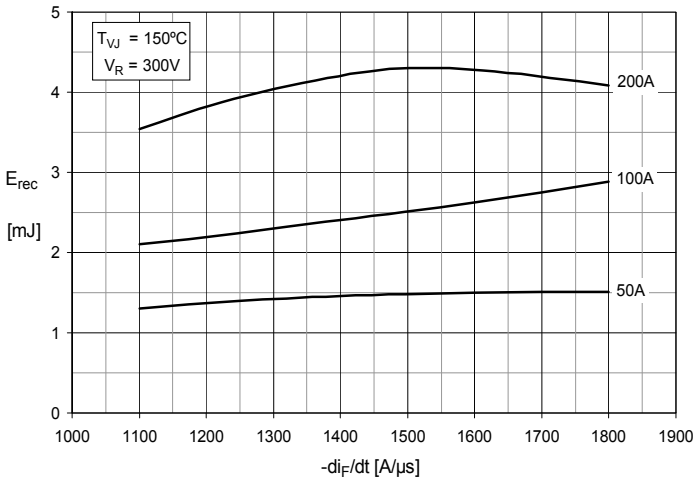


Fig. 26. Typ. Recovery Energy E_{rec} vs. $-di_F/dt$



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